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TRANSMITTAL FORM (to be used for all correspondence after initial filing)	Application Number	09/557,961	
	Filing Date	April 25, 2001	
	First Named Inventor	Kunihiro TAKATANI	
	Group Art Unit	2811	
	Examiner Name	Donghee Kang	
Total Number Of Pages In This Submission	8	Attorney Docket No.	245402001600

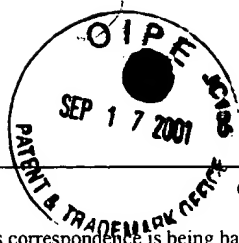
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Firm or Individual Name	Jonathan Bockman Registration No. 45,640 Morrison & Foerster LLP 2000 Pennsylvania Avenue, N.W. Washington, D.C. 20006-1888 (202) 778-1604
Signature	
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Faith Jacks
Faith Jacks

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of:

Kunihiro TAKATANI

Serial No.: 09/557,961

Filing Date: April 25, 2000

For: ELECTRODE STRUCTURE ON P-TYPE III GROUP NITRIDE SEMICONDUCTOR LAYER AND FORMATION METHOD THEREOF

Examiner: Donghee Kang

Group Art Unit: 2811

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AMENDMENT UNDER 37 CFR 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated June 15, 2001, please amend this application as follows:

AMENDMENTS

In the Claims:

Subt B'
Please amend claim 1 as follows:

- A'*
1. (Amended) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,